

isc Silicon NPN Power Transistor

2SC2484

DESCRIPTION

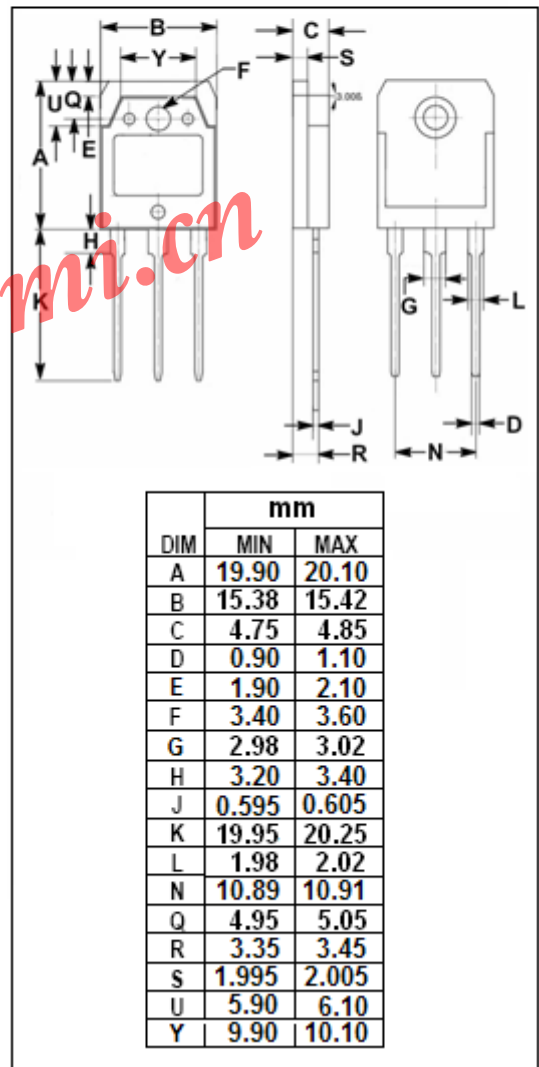
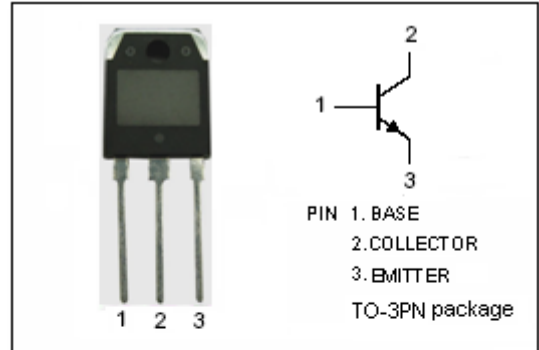
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 80V(\text{Min})$
- High Power Dissipation
- Complement to Type 2SA1060

APPLICATIONS

- Designed for high power audio frequency amplifier applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	80	V
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	5	A
$I_{CM}$	Collector Current-Peak	8	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	60	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=30\text{mA}; I_B=0$	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$			2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}; V_{CE}=5\text{V}$			1.8	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			50	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=3\text{V}; I_C=0$			50	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C=20\text{mA}; V_{CE}=5\text{V}$	20			
$h_{FE-2}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	40		220	
$h_{FE-3}$	DC Current Gain	$I_C=3\text{A}; V_{CE}=5\text{V}$	20			
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=5\text{V}$		20		MHz

◆  $h_{FE-2}$  Classifications

R	Q	P
40-80	60-120	100-200